

# NXH160T120L2Q1PG, NXH160T120L2Q1SG

---

## Q1PACK Module

This high-density, integrated power module combines high-performance IGBTs with rugged anti-parallel diodes.

### Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Module Design Offers High Power Density
- Low Inductive Layout
- Q1PACK Package with Press-

# NXH160T120L2Q1PG, NXH160T120L2Q1SG

Forward Current, DC @  $T_h = 80^\circ\text{C}$

$I_F$

20

A

Repetitive Peak Forward Current  
 $T_{\text{pulse}}$  limited by T

# NXH160T120L2Q1PG, NXH160T120L2Q1SG

**Table 1. ABSOLUTE MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
<b>HALFBRIDGE DIODE (D5, D8)</b>			
Junction Temperature	$T_J$	150	°C
<b>THERMAL PROPERTIES</b>			
Operating Temperature under switching condition	$T_{VJ\ OP}$	-40 to ( $T_{jmax}-25$ )	°C
Storage Temperature range	$T_{stg}$	-40 to 125	°C
<b>INSULATION PROPERTIES</b>			
Isolation test voltage, t = 1 sec, 60 Hz/50 Hz	$V_{is}$	3000	$V_{RMS}$
Creepage distance		12.7	mm
Clearance		8.06	mm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter
-----------



**NXH160T120L2Q1PG, NXH160T120L2Q1SG**

**TYPICAL CHARACTERISTICS –**

**NXH160T120L2Q1PG, NXH160T120L2Q1SG**

**NXH160T120L2Q1PG, NXH160T120L2Q1SG**

**NXH160T120L2Q1PG, NXH160T120L2Q1SG**

**TYPICAL CHARACTERISTICS –**

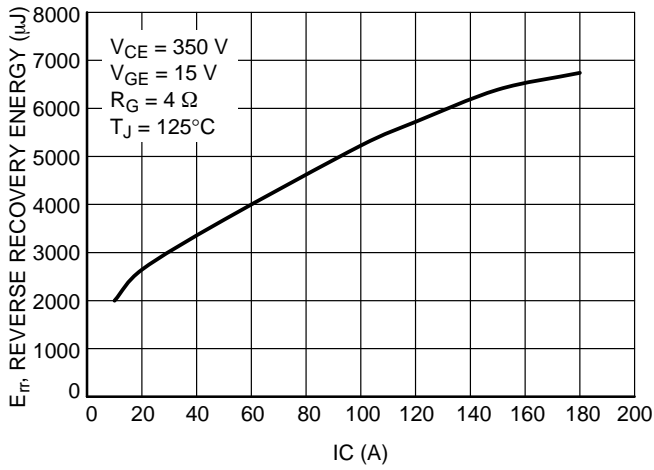


**NXH160T120L2Q1PG, NXH160T120L2Q1SG**

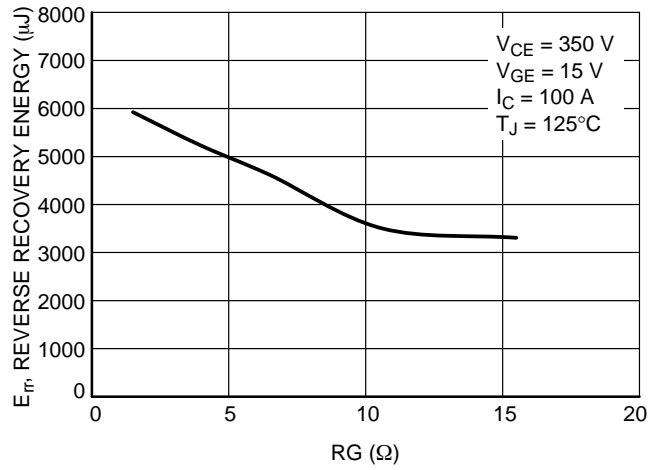


# NXH160T120L2Q1PG, NXH160T120L2Q1SG

## TYPICAL CHARACTERISTICS – NEUTRAL POINT IGBT AND HALF BRIDGE FORWARD DIODE



**Figure 29. Typical Reverse Recovery Energy Loss vs. IC**



**Figure 30. Typical Reverse Recovery Energy Loss vs. R<sub>G</sub>**


**NXH160T120L2Q1PG, NXH160T120L2Q1SG**

**TYPICAL CHARACTERISTICS – NEUTRAL POINT IGBT AND HALF BRIDGE FORWARD DIODE**


**NXH160T120L2Q1PG, NXH160T120L2Q1SG**



# NXH160T120L2Q1PG, NXH160T120L2Q1SG

## TYPICAL CHARACTERISTICS – NEUTRAL POINT INVERSE DIODE

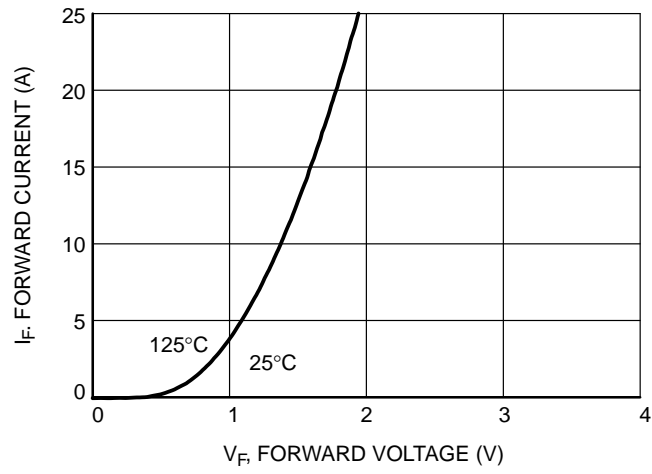
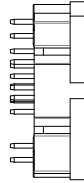
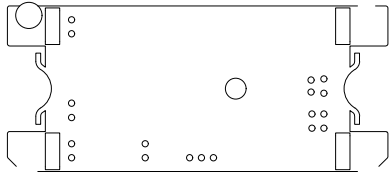


Figure 47. Diode Forward Characteristics

PIM30, 71x37.4

5	0.80
6	-1.70
7	-11.05 11.55
8	
9	
10	
11	
12	-26.50
13	
<b>PIM30, 71x37.4</b>	
<b>CASE 180AQ</b>	
ISSUE A	

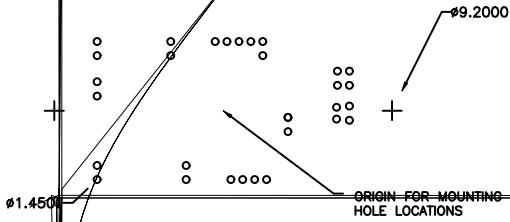
DATE 25 JUN 2018



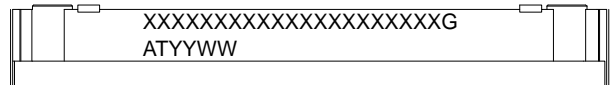
TOP VIEW

END VIEW

SIDE VIEW



**GENERIC MARKING DIAGRAM\***



- XXXXX = Specific Device Code
- G = Pb-Free Package
- AT = Assembly & Test Site Code
- YYWW = Year and Work Week Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



onsemi

onsemi

onsemi

onsemi

— — — — —  
— onsemi —  
— onsemi —

onsemi

onsemi

onsemi

